Day : Wednesday

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Inventor Name Search Result

Your Search was:

Last Name = SAKURADA First Name = MASAHIRO

Application#	Patent#	Status	Date Filed	Title	Inventor Name
08498894	5609682	150	07/06/1995	A METHOD FOR THE PREPARATION OF SILICON SINGLE CRYSTAL	SAKURADA, MASAHIRO
08565100	5667584	150	11/30/1995	METHOD FOR THE PREPARATION OF A SINGLE CRYSTAL OF SILICON WITH DECREASED CRYSTAL DEFECTS	SAKURADA, MASAHIRO
08655810	5817171	150	05/31/1996	APPARATUS AND METHOD FOR PRODUCING SINGLE CRYSTAL USING CZOCHRALSKI TECHNIQUE	SAKURADA, MASAHIRO
08660198	5728211	250	06/03/1996	SILICON SINGLE CRYSTAL WITH LOW DEFECT DENSITY AND METHOD OF PRODUCING SAME	SAKURADA, MASAHIRO
08666654	5704973	150	06/18/1996	AN APPARATUS AND METHOD FOR THE UNIFORM DISTRIBUTION OF CRYSTAL DEFECTS UPON A SILICON SINGLE CRYSTAL	SAKURADA, MASAHIRO
08768282	5730800	150	12/17/1996	FUSED SILICA GLASS CRUCIBLE	SAKURADA, MASAHIRO
08798472	5948163	250		APPARATUS FOR MANUFACTURING CRYSTALS ACCORDING TO THE CZOCHRALSKI METHOD, AND CRYSTALS MANUFACTURED BY THE MANUFACTURING METHOD	SAKURADA, MASAHIRO
09090400	5938842	150		METHOD FOR PRODUCING A SINGLE CRYSTAL USING	SAKURADA, MASAHIRO

				CZOCHRALSKI TECHNIQUE	
09125339	6071337	150		APPARATUS AND METHOD	SAKURADA, MASAHIRO
09232561	6174364	150	01/15/1999	METHOD FOR PRODUCING SILICON MONOCRYSTAL AND SILICON MONOCRYSTAL WAFER	SAKURADA, MASAHIRO
09328278	6190452	150	06/08/1999	SILICON SINGLE CRYSTAL WAFER AND METHOD FOR PRODUCING IT	SAKURADA, MASAHIRO
09646713	6565822	150	09/21/2000	EPITAXIAL SILICON WAFER, METHOD FOR PRODUCING THE SAME AND SUBTRATE FOR EPITAXIAL SILICON WAFER	SAKURADA, MASAHIRO
09727275	6482260	150	11/30/2000	SILICON SINGLE CRYSTAL WAFER AND A METHOD FOR PRODUCING IT	SAKURADA, MASAHIRO
10204935	6913646	150	08/27/2002	SILICON SINGLE CRYSTAL WAFER AND METHOD FOR PRODUCING SILICON SINGLE CRYSTAL	SAKURADA, MASAHIRO
10312921	6893499	150	12/26/2002	SILICON SINGLE CRYSTAL WAFER AND METHOD FOR MANUFACTURING THE SAME	SAKURADA, MASAHIRO
10500580	7129123	150	07/01/2004	AN SOI WAFER AND A METHOD FOR PRODUCING AN SOI WAFER	SAKURADA, MASAHIRO
10512470	7294196	150	10/26/2004	A SILICON SINGLE CRYSTAL WAFER, AN EPITAXIAL WAFER AND A METHOD FOR PRODUCING A SILICON SINGLE CRYSTAL	SAKURADA, MASAHIRO
10516347	7258744	150	11/30/2004	GRAPHITE HEATER FOR PRODUCING SINGLE CRYSTAL, APPARATUS FOR PRODUCING SINGLE CRYSTAL, AND METHOD FOR PRODUCING SINGLE CRYSTAL	SAKURADA, MASAHIRO
10530557	Not	95	04/07/2005	ANNEALED WAFER AND	SAKURADA, ·

	Issued			METHOD FOR MANUFACTURING THE SAME	MASAHIRO
10538878	7214268	150		METHOD OF PRODUCING P- DOPED SILICON SINGLE CRYSTAL AND P-DOPED N- TYPE SILICON SINGLE CRYSTAL WAFER	SAKURADA, MASAHIRO
10542376	Not Issued	71		AN SOI WAFER AND A METHOD FOR PRODUCING THE SAME	SAKURADA, MASAHIRO
10546693	Not Issued	61		An soi wafer and a method for producing the same	SAKURADA, MASAHIRO
10560581	Not Issued	71		Method for producing a single crystal and a single crystal	SAKURADA, MASAHIRO
10561205	Not Issued	93		A METHOD FOR PRODUCING A SINGLE CRYSTAL AND A SINGLE CRYSTAL	SAKURADA, MASAHIRO
10561865	7226507	150	02/20/2006	METHOD FOR PRODUCING SINGLE CRYSTAL AND SINGLE CRYSTAL	SAKURADA, MASAHIRO
11664436	Not Issued	20	03/30/2007	Apparatus for Producing a Single Crystal	SAKURADA, MASAHIRO

Inventor Search Completed: No Records to Display.

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